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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	792
Total RAM Bits	-
Number of I/O	120
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	201-VFBGA, CSBGA
Supplier Device Package	201-CSP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp030v5-cs201

Ramping up (V2 devices): $0.65\text{ V} < \text{trip_point_up} < 1.05\text{ V}$

Ramping down (V2 devices): $0.55\text{ V} < \text{trip_point_down} < 0.95\text{ V}$

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75\text{ V} \pm 0.25\text{ V}$ for V5 devices, and $0.75\text{ V} \pm 0.2\text{ V}$ for V2 devices), the PLL output lock signal goes Low and/or the output clock is lost. Refer to the "Brownout Voltage" section in the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *IGLOO PLUS Device Family User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers
3. Output buffers, after 200 ns delay from input buffer activation

To make sure the transition from input buffers to output buffers is clean, ensure that there is no path longer than 100 ns from input buffer to output buffer in your design.

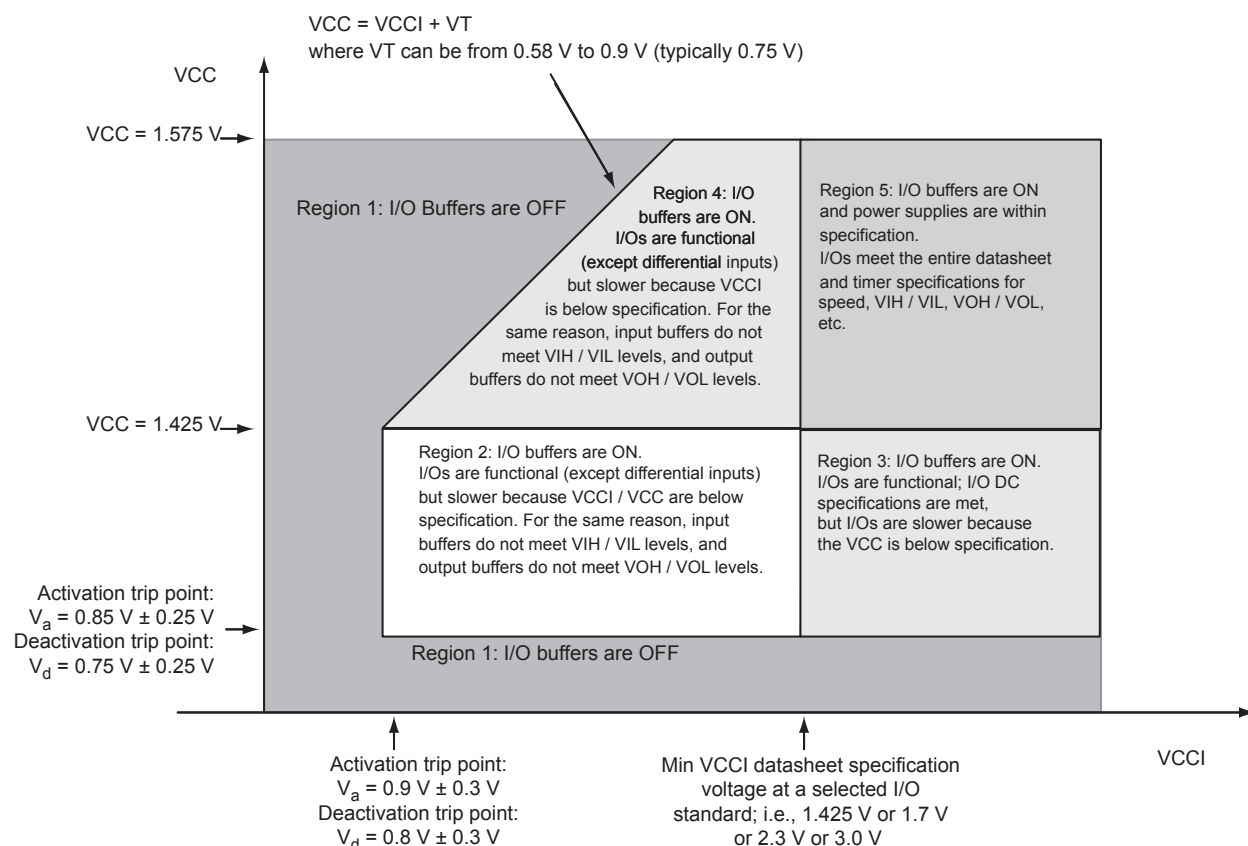


Figure 2-1 • V5 Devices – I/O State as a Function of VCCI and VCC Voltage Levels

**Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO PLUS Devices
For IGLOO PLUS V2 Devices, 1.2 V Core Supply Voltage**

Parameter	Definition	Device-Specific Dynamic Power (μW/MHz)		
		AGLP125	AGLP060	AGLP030
PAC1	Clock contribution of a Global Rib	2.874	1.727	0.000 ¹
PAC2	Clock contribution of a Global Spine	1.264	1.244	2.241
PAC3	Clock contribution of a VersaTile row	0.963	0.975	0.981
PAC4	Clock contribution of a VersaTile used as a sequential module	0.098	0.096	0.096
PAC5	First contribution of a VersaTile used as a sequential module	0.018	0.018	0.018
PAC6	Second contribution of a VersaTile used as a sequential module	0.203	0.203	0.203
PAC7	Contribution of a VersaTile used as a combinatorial module	0.160	0.170	0.158
PAC8	Average contribution of a routing net	0.679	0.686	0.748
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-9		
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-14 on page 2-9		
PAC11	Average contribution of a RAM block during a read operation	25.00		
PAC12	Average contribution of a RAM block during a write operation	30.00		
PAC13	Dynamic contribution for PLL	2.10		

Note: 1. There is no Center Global Rib present in AGLP030, and thus it starts directly at the spine resulting in 0μW/MHz.

**Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices
For IGLOO PLUS V2 Devices, 1.2 V Core Supply Voltage**

Parameter	Definition	Device-Specific Static Power (mW)		
		AGLP125	AGLP060	AGLP030
PDC1	Array static power in Active mode	See Table 2-12 on page 2-8		
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-7		
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7		
PDC4	Static PLL contribution	0.90 ¹		
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-12 on page 2-8		

Notes:

1. This is the minimum contribution of the PLL when operating at lowest frequency.
2. For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or the SmartPower tool in Libero SoC software.

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ²	Slew Rate	VIL		VIH		VOL	VOH	IOL ¹	IOH ¹
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTTL / 3.3 V LVC MOS	12 mA	12 mA	High	−0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVC MOS Wide Range ³	100 μ A	12 mA	High	−0.3	0.8	2	3.6	0.2	VDD 3 0.2	0.1	0.1
2.5 V LVC MOS	12 mA	12 mA	High	−0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVC MOS	8 mA	8 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	8	8
1.5 V LVC MOS	4 mA	4 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4
1.2 V LVC MOS ⁴	2 mA	2 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVC MOS Wide Range ^{4,5}	100 μ A	2 mA	High	−0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI − 0.1	0.1	0.1

Notes:

1. Currents are measured at 85°C junction temperature.
2. Note that 1.2 V LVC MOS and 3.3 V LVC MOS wide range are applicable to 100 μ A drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.
3. All LVC MOS 3.3 V software macros support LVC MOS 3.3 V wide range as specified in the JESD-8B specification.
4. Applicable to IGLOO PLUS V2 devices operating at $VCC_I \geq VCC$.
5. All LVC MOS 1.2 V software macros support LVC MOS 1.2 V wide range as specified in the JESD8-12 specification.

Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade
Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.98	2.31	0.19	0.99	1.37	0.67	2.34	1.86	2.65	3.38	ns
3.3 V LVCMOS Wide Range ²	100 μA	12 mA	High	5 pF	–	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns
2.5 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.98	2.29	0.19	1.19	1.40	0.67	2.32	1.94	2.65	3.27	ns
1.8 V LVCMOS	8 mA	8 mA	High	5 pF	–	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns
1.5 V LVCMOS	4 mA	4 mA	High	5 pF	–	0.98	2.71	0.19	1.26	1.80	0.67	2.75	2.39	2.78	3.15	ns
1.2 V LVCMOS	2 mA	2 mA	High	5 pF	–	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns
1.2 V LVCMOS Wide Range ³	100 μA	2 mA	High	5 pF	–	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.
4. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

VCCI	$R_{(WEAK\ PULL-UP)}^1$ (Ω)		$R_{(WEAK\ PULL-DOWN)}^2$ (Ω)	
	Min.	Max.	Min.	Max.
3.3 V	10 K	45 K	10 K	45 K
3.3 V (wide range I/Os)	10 K	45 K	10 K	45 K
2.5 V	11 K	55 K	12 K	74 K
1.8 V	18 K	70 K	17 K	110 K
1.5 V	19 K	90 K	19 K	140 K
1.2 V	25 K	110 K	25 K	150 K
1.2 V (wide range I/Os)	19 K	110 K	19 K	150 K

Notes:

1. $R_{(WEAK\ PULL-UP-MAX)} = (VCCImax - VOHspec) / I_{(WEAK\ PULL-UP-MIN)}$
2. $R_{(WEAK\ PULLDOWN-MAX)} = (VOLspec) / I_{(WEAK\ PULLDOWN-MIN)}$

Table 2-30 • I/O Short Currents IOSH/IOSL

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	27	25
	4 mA	27	25
	6 mA	54	51
	8 mA	54	51
	12 mA	109	103
	16 mA	109	103
3.3 V LVCMOS Wide Range	100 μ A	Same as equivalent software default drive	
2.5 V LVCMOS	2 mA	18	16
	4 mA	18	16
	6 mA	37	32
	8 mA	37	32
	12 mA	74	65
1.8 V LVCMOS	2 mA	11	9
	4 mA	22	17
	6 mA	44	35
	8 mA	44	35
1.5 V LVCMOS	2 mA	16	13
	4 mA	33	25
1.2 V LVCMOS	2 mA	26	20
1.2 V LVCMOS Wide Range	100 μ A	26	20

Note: * $T_J = 100^\circ\text{C}$

Applies to 1.2 V DC Core Voltage

Table 2-44 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	4 mA	STD	0.98	6.68	0.19	1.32	1.92	0.67	6.68	5.74	3.13	3.47	ns
100 μA	6 mA	STD	0.98	5.51	0.19	1.32	1.92	0.67	5.51	4.94	3.48	4.11	ns
100 μA	8 mA	STD	0.98	5.51	0.19	1.32	1.92	0.67	5.51	4.94	3.48	4.11	ns
100 μA	12 mA	STD	0.98	4.75	0.19	1.32	1.92	0.67	4.75	4.36	3.73	4.52	ns
100 μA	16 mA	STD	0.98	4.75	0.19	1.32	1.92	0.67	4.75	4.36	3.73	4.52	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-45 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	4 mA	STD	0.98	4.16	0.19	1.32	1.92	0.67	4.16	3.32	3.12	3.66	ns
100 μA	6 mA	STD	0.98	3.54	0.19	1.32	1.92	0.67	3.54	2.79	3.48	4.31	ns
100 μA	8 mA	STD	0.98	3.54	0.19	1.32	1.92	0.67	3.54	2.79	3.48	4.31	ns
100 μA	12 mA	STD	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns
100 μA	16 mA	STD	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
3. Software default selection highlighted in gray.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-58 • Minimum and Maximum DC Input and Output Levels

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	−0.3	0.35 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

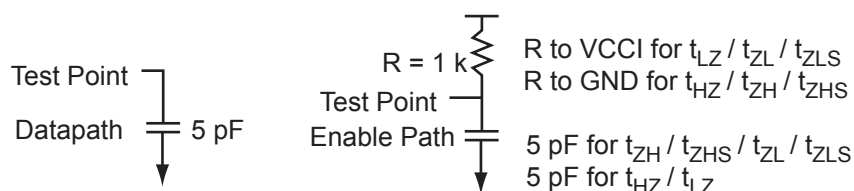


Figure 2-10 • AC Loading

Table 2-59 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.5	0.75	5

Note: *Measuring point = V_{trip} . See [Table 2-23 on page 2-20](#) for a complete table of trip points.

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-70 • 1.2 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	2 mA	STD	0.98	8.27	0.19	1.57	2.34	0.67	7.94	6.77	3.00	3.11	ns

Notes:

1. The minimum drive strength for any LVCMOS 1.2 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-71 • 1.2 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	2 mA	STD	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

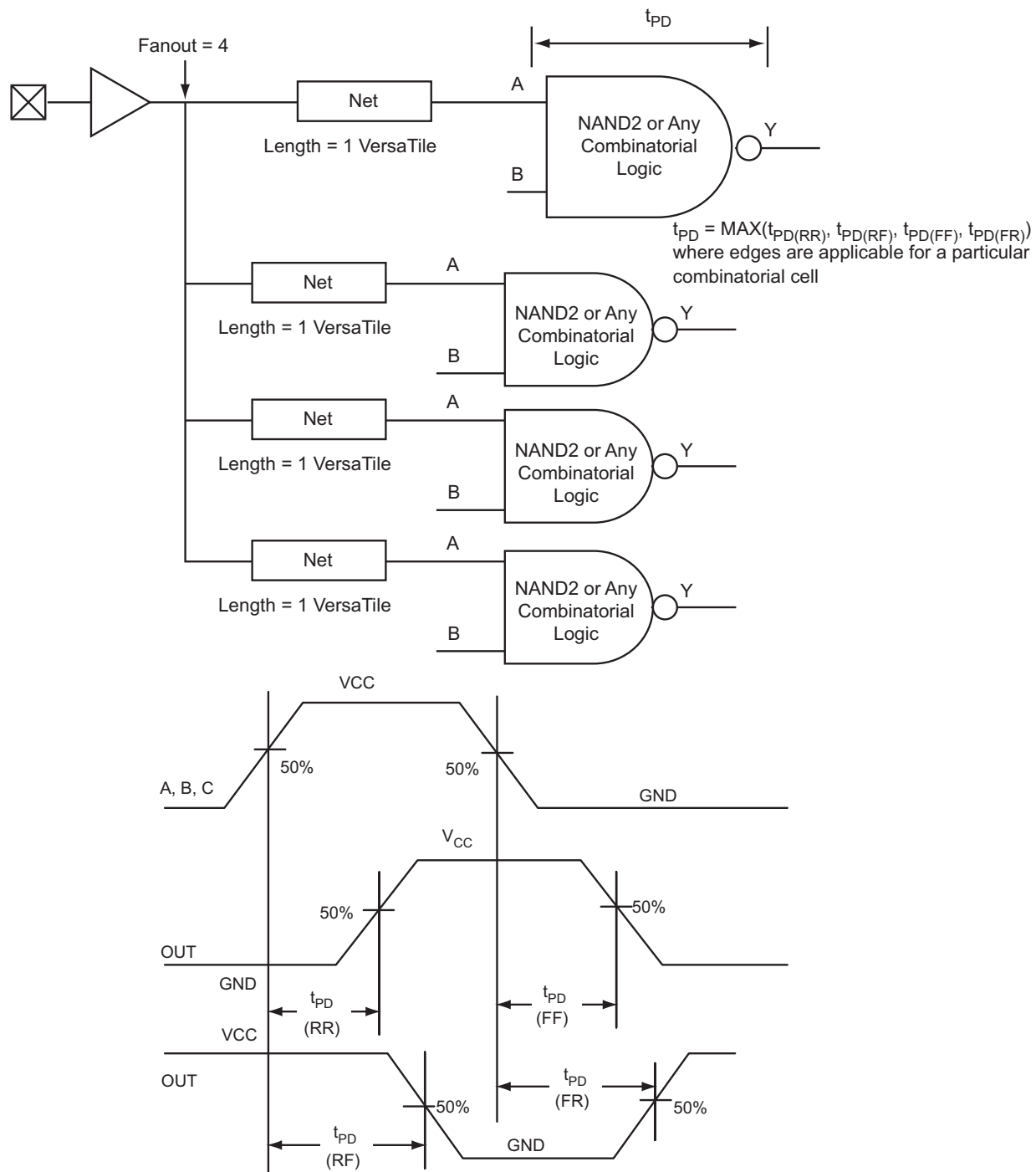
Notes:

1. The minimum drive strength for any LVCMOS 1.2 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.
3. Software default selection highlighted in gray.

Table 2-73 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OERMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OERMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IERMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-13 on page 2-43 for more information.


Figure 2-18 • Timing Model and Waveforms

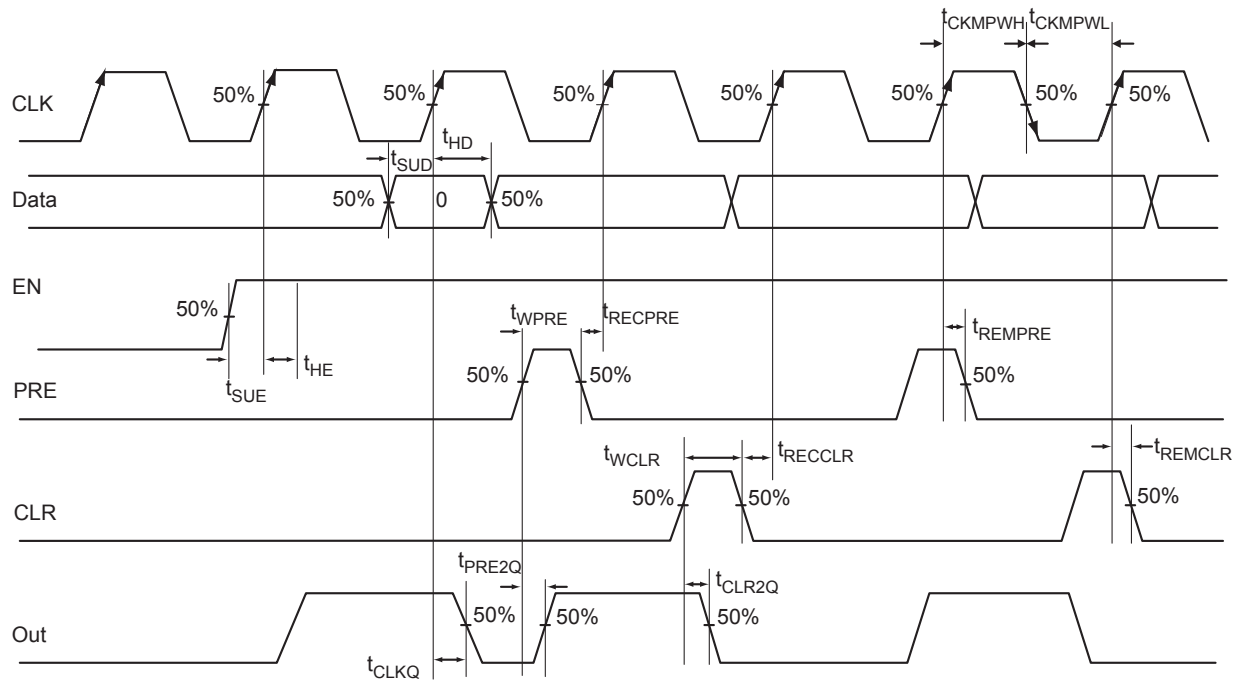


Figure 2-20 • Timing Model and Waveforms

Timing Characteristics

1.5 V DC Core Voltage

Table 2-82 • Register Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.89	ns
t_{SUD}	Data Setup Time for the Core Register	0.81	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.73	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.60	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.62	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.23	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.30	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.30	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.56	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.56	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-86 • AGLP125 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.36	1.71	ns
t_{RCKH}	Input High Delay for Global Clock	1.39	1.82	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

1.2 V DC Core Voltage

Table 2-87 • AGLP030 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.80	2.09	ns
t_{RCKH}	Input High Delay for Global Clock	1.88	2.27	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.39	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

Table 2-91 • IGLOO PLUS CCC/PLL Specification
For IGLOO PLUS V2 Devices, 1.2 V DC Core Supply Voltage

Parameter	Min.	Typ.	Max.	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		160	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		160	MHz
Delay Increments in Programmable Delay Blocks ^{1, 2}		580 ³		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Serial Clock (SCLK) for Dynamic PLL ^{4, 5}			60	MHz
Input Cycle-to-Cycle Jitter (peak magnitude)			.25	ns
Acquisition Time				
LockControl = 0			300	μs
LockControl = 1			6.0	ms
Tracking Jitter ⁶				
LockControl = 0			4	ns
LockControl = 1			3	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1 ^{1, 2}	2.3		20.86	ns
Delay Range in Block: Programmable Delay 2 ^{1, 2}	0.863		20.86	ns
Delay Range in Block: Fixed Delay ^{1, 2}		5.7		ns
VCO Output Peak-to-Peak Period Jitter F_{CCC_OUT} ⁷	Maximum Peak-to-Peak Period Jitter ^{7, 8, 9}			
	SSO ≤ 2	SSO ≤ 4	SSO ≤ 8	SSO ≤ 16
0.75 MHz to 50 MHz	0.50%	1.20%	2.00%	3.00%
50 MHz to 160 MHz	2.50%	5.00%	7.00%	15.00%

Notes:

1. This delay is a function of voltage and temperature. See [Table 2-6 on page 2-6](#) and [Table 2-7 on page 2-6](#) for deratings.
2. $T_J = 25^\circ\text{C}$, $V_{CC} = 1.2\text{ V}$
3. When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the online help associated with the core for more information.
4. Maximum value obtained for a STD speed grade device in Worst Case Commercial Conditions. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) and [Table 2-7 on page 2-6](#) for derating values.
5. The AGLP030 device does not support PLL.
6. Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by period jitter parameter.
7. VCO output jitter is calculated as a percentage of the VCO frequency. The jitter (in ps) can be calculated by multiplying the VCO period by the per cent jitter. The VCO jitter (in ps) applies to CCC_OUT regardless of the output divider settings. For example, if the jitter on VCO is 300 ps, the jitter on CCC_OUT is also 300 ps, regardless of the output divider settings.
8. Measurements are done with LVTTTL 3.3 V, 8 mA, I/O drive strength and high slew rate. $V_{CC}/V_{CCPLL} = 1.14\text{ V}$, $V_{CCI} = 3.3\text{ V}$, VQ/PQ/TQ type of packages, 20 pF load.
9. SSO are outputs that are synchronous to a single clock domain, and have their clock-to-out times within $\pm 200\text{ ps}$ of each other. Switching I/Os are placed outside of the PLL bank. Refer to the "Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout" section in the [IGLOO PLUS FPGA Fabric User's Guide](#)

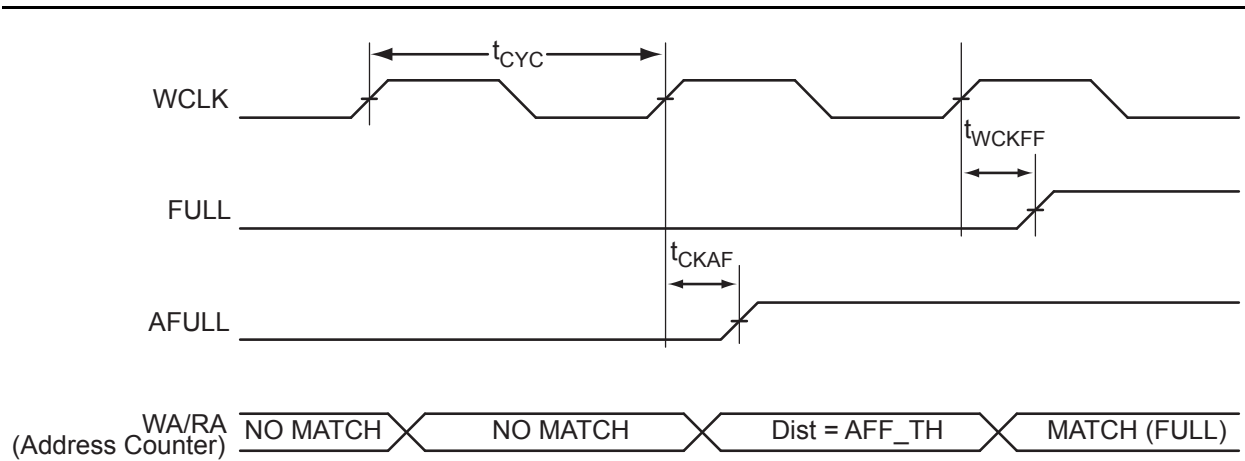


Figure 2-34 • FIFO FULL Flag and AFULL Flag Assertion

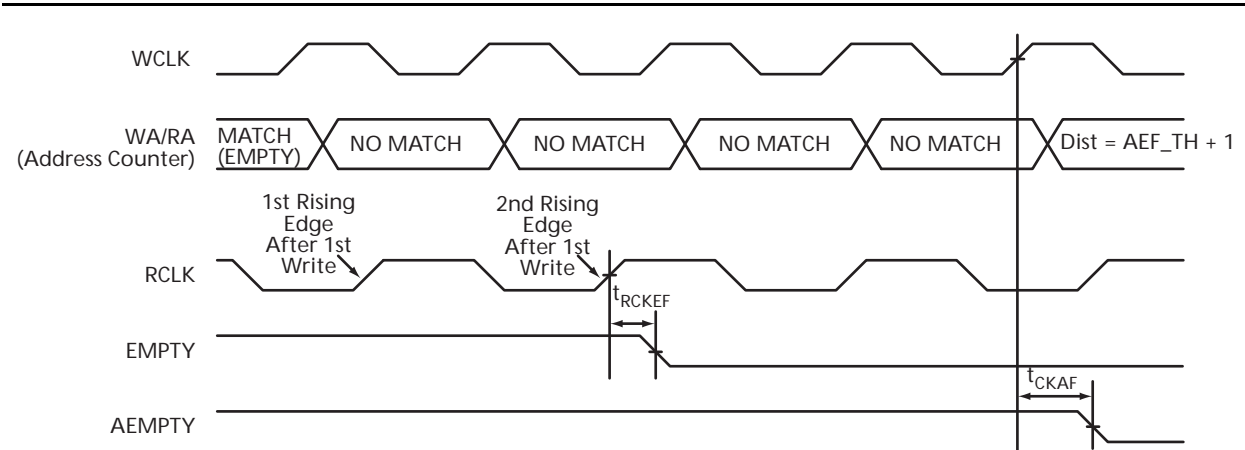


Figure 2-35 • FIFO EMPTY Flag and AEMPTY Flag Deassertion

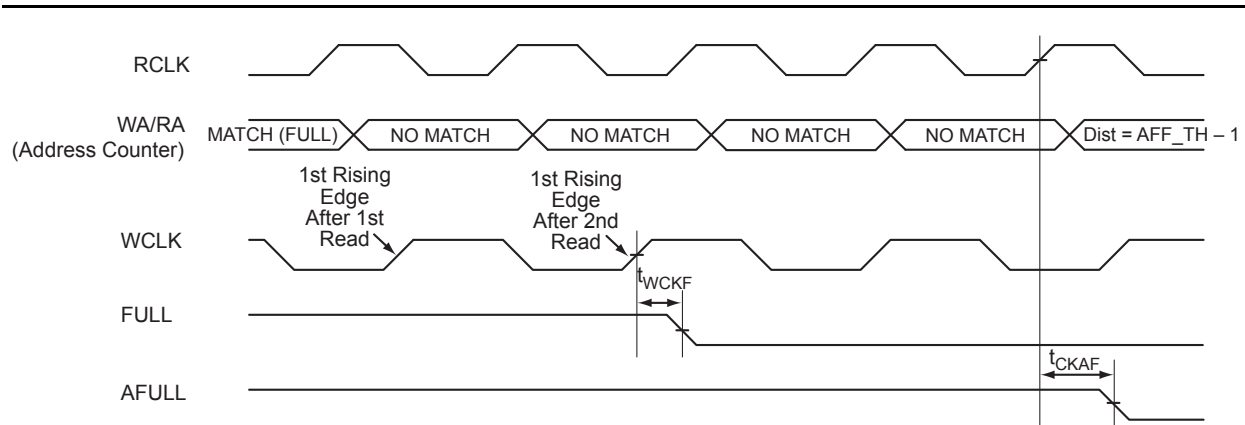


Figure 2-36 • FIFO FULL Flag and AFULL Flag Deassertion

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK

Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements. Refer to [Table 3-2](#) for more information.

Table 3-2 • Recommended Tie-Off Values for the TCK and TRST Pins

VJTAG	Tie-Off Resistance
VJTAG at 3.3 V	200 Ω to 1 k Ω
VJTAG at 2.5 V	200 Ω to 1 k Ω
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 k Ω

Notes:

1. Equivalent parallel resistance if more than one device is on the JTAG chain
2. The TCK pin can be pulled up/down.
3. The TRST pin is pulled down.

TDI

Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO

Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS

Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST

Boundary Scan Reset Pin

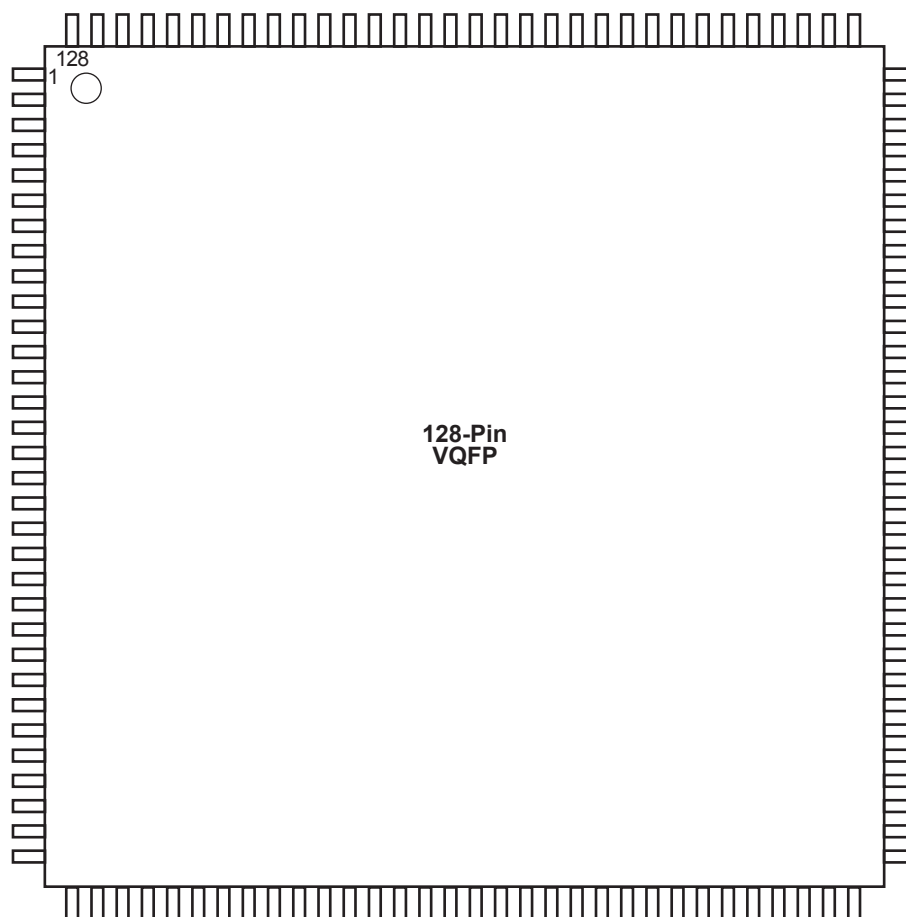
The TRST pin functions as an active-low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from [Table 3-2](#) and must satisfy the parallel resistance value requirement. The values in [Table 3-2](#) correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

In critical applications, an upset in the JTAG circuit could allow entrance to an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements.

4 – Package Pin Assignments

VQ128



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

Pin information is in the "Pin Descriptions" chapter of the *IGLOO PLUS FPGA Fabric User's Guide*.

VQ128	
Pin Number	AGLP030 Function
106	IO26RSB0
107	IO25RSB0
108	IO23RSB0
109	IO22RSB0
110	IO21RSB0
111	IO19RSB0
112	IO18RSB0
113	VCC
114	IO17RSB0
115	IO16RSB0
116	IO14RSB0
117	IO13RSB0
118	IO12RSB0
119	IO10RSB0
120	IO09RSB0
121	VCCIB0
122	GND
123	IO07RSB0
124	IO05RSB0
125	IO03RSB0
126	IO02RSB0
127	IO01RSB0
128	IO00RSB0

VQ176	
Pin Number	AGLP060 Function
1	GAA2/IO156RSB3
2	IO155RSB3
3	GAB2/IO154RSB3
4	IO153RSB3
5	GAC2/IO152RSB3
6	GND
7	VCCIB3
8	IO149RSB3
9	IO147RSB3
10	IO145RSB3
11	IO144RSB3
12	IO143RSB3
13	VCC
14	IO141RSB3
15	GFC1/IO140RSB3
16	GFB1/IO138RSB3
17	GFB0/IO137RSB3
18	VCOMPLF
19	GFA1/IO136RSB3
20	VCCPLF
21	GFA0/IO135RSB3
22	GND
23	VCCIB3
24	GFA2/IO134RSB3
25	GFB2/IO133RSB3
26	GFC2/IO132RSB3
27	IO131RSB3
28	IO130RSB3
29	IO129RSB3
30	IO127RSB3
31	IO126RSB3
32	IO125RSB3
33	IO123RSB3
34	IO122RSB3
35	IO121RSB3

VQ176	
Pin Number	AGLP060 Function
36	IO119RSB3
37	GND
38	VCCIB3
39	GEC1/IO116RSB3
40	GEB1/IO114RSB3
41	GEC0/IO115RSB3
42	GEB0/IO113RSB3
43	GEA1/IO112RSB3
44	GEA0/IO111RSB3
45	GEA2/IO110RSB2
46	NC
47	FF/GEB2/IO109RSB2
48	GEC2/IO108RSB2
49	IO106RSB2
50	IO107RSB2
51	IO104RSB2
52	IO105RSB2
53	IO102RSB2
54	IO103RSB2
55	GND
56	VCCIB2
57	IO101RSB2
58	IO100RSB2
59	IO99RSB2
60	IO98RSB2
61	IO97RSB2
62	IO96RSB2
63	IO95RSB2
64	IO94RSB2
65	IO93RSB2
66	VCC
67	IO92RSB2
68	IO91RSB2
69	IO90RSB2

VQ176	
Pin Number	AGLP060 Function
70	IO89RSB2
71	IO88RSB2
72	IO87RSB2
73	IO86RSB2
74	IO85RSB2
75	IO84RSB2
76	GND
77	VCCIB2
78	IO83RSB2
79	IO82RSB2
80	GDC2/IO80RSB2
81	IO81RSB2
82	GDA2/IO78RSB2
83	GDB2/IO79RSB2
84	NC
85	NC
86	TCK
87	TDI
88	TMS
89	VPUMP
90	TDO
91	TRST
92	VJTAG
93	GDA1/IO76RSB1
94	GDC0/IO73RSB1
95	GDB1/IO74RSB1
96	GDC1/IO72RSB1
97	VCCIB1
98	GND
99	IO70RSB1
100	IO69RSB1
101	IO67RSB1
102	IO66RSB1
103	IO65RSB1
104	IO63RSB1

CS201		CS201		CS201	
Pin Number	AGLP060 Function	Pin Number	AGLP060 Function	Pin Number	AGLP060 Function
A1	IO150RSB3	C6	IO07RSB0	F3	IO145RSB3
A2	GAA0/IO00RSB0	C7	IO16RSB0	F4	IO147RSB3
A3	GAC0/IO04RSB0	C8	IO21RSB0	F6	GND
A4	IO08RSB0	C9	IO28RSB0	F7	VCC
A5	IO11RSB0	C10	GBB1/IO33RSB0	F8	VCCIB0
A6	IO15RSB0	C11	GBA1/IO35RSB0	F9	VCCIB0
A7	IO17RSB0	C12	GBB2/IO38RSB1	F10	VCCIB0
A8	IO18RSB0	C13	GND	F12	IO47RSB1
A9	IO22RSB0	C14	IO48RSB1	F13	IO45RSB1
A10	IO26RSB0	C15	IO39RSB1	F14	GCC1/IO52RSB1
A11	IO29RSB0	D1	IO146RSB3	F15	GCA1/IO56RSB1
A12	GBC1/IO31RSB0	D2	IO144RSB3	G1*	VCOMPLF
A13	GBA2/IO36RSB1	D3	IO148RSB3	G2	GFB0/IO137RSB3
A14	IO41RSB1	D4	GND	G3	GFC0/IO139RSB3
A15	NC	D5	GAB0/IO02RSB0	G4	IO143RSB3
B1	IO151RSB3	D6	GAC1/IO05RSB0	G6	VCCIB3
B2	GAB2/IO154RSB3	D7	IO14RSB0	G7	GND
B3	IO06RSB0	D8	IO19RSB0	G8	VCC
B4	IO09RSB0	D9	GBC0/IO30RSB0	G9	GND
B5	IO13RSB0	D10	GBB0/IO32RSB0	G10	GND
B6	IO10RSB0	D11	GBA0/IO34RSB0	G12	IO50RSB1
B7	IO12RSB0	D12	GND	G13	GCB1/IO54RSB1
B8	IO20RSB0	D13	GBC2/IO40RSB1	G14	GCC2/IO60RSB1
B9	IO23RSB0	D14	IO51RSB1	G15	GCA2/IO58RSB1
B10	IO25RSB0	D15	IO44RSB1	H1*	VCCPLF
B11	IO24RSB0	E1	IO142RSB3	H2	GFA1/IO136RSB3
B12	IO27RSB0	E2	IO149RSB3	H3	GFB1/IO138RSB3
B13	IO37RSB1	E3	IO153RSB3	H4	NC
B14	IO46RSB1	E4	GAC2/IO152RSB3	H6	VCCIB3
B15	IO42RSB1	E12	IO43RSB1	H7	GND
C1	IO155RSB3	E13	IO49RSB1	H8	VCC
C2	GAA2/IO156RSB3	E14	GCC0/IO53RSB1	H9	GND
C3	GND	E15	GCB0/IO55RSB1	H10	VCCIB1
C4	GAA1/IO01RSB0	F1	IO141RSB3	H12	GCB2/IO59RSB1
C5	GAB1/IO03RSB0	F2	GFC1/IO140RSB3	H13	GCA0/IO57RSB1

Note: *Pin numbers G1 and H1 must be connected to ground because a PLL is not supported for AGLP060-CS/G201.



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